

# PU7456

## Silicon N-Channel Power F-MOS (with built-in zener diode)

### ■ Features

- High avalanche energy capability
- Withstanding high electrostatic voltage
- No secondary breakdown
- High breakdown voltage, large allowable power dissipation
- Low-voltage drive possible

### ■ Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

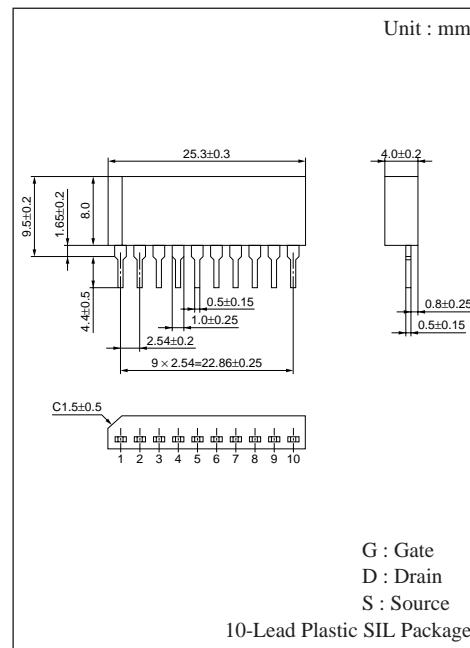
### ■ Absolute Maximum Ratings ( $T_c = 25^\circ\text{C}$ )

Parameter	Symbol	Rating	Unit
Drain-Source breakdown voltage	$V_{DSS}$	$35 \pm 10$	V
Gate-Source voltage	$V_{GSS}$	$\pm 20$	V
Drain current	DC	$I_D$	A
	Pulse	$I_{DP}$	A
Avalanche energy capability	Non repetition	EAS *	mJ
	Repetition	EAR	mJ
Allowable power dissipation	$T_c = 25^\circ\text{C}$	15	W
	$T_a = 25^\circ\text{C}$	3.5	
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

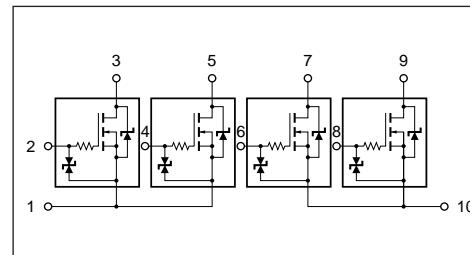
\*  $L=11.2\text{mH}$ ,  $I_L=6\text{A}$ ,  $V_{DD}=50\text{V}$ , 1 pulse

### ■ Electrical Characteristics ( $T_c = 25^\circ\text{C}$ )

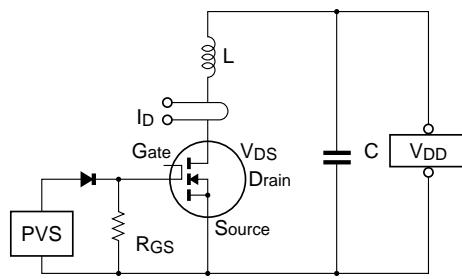
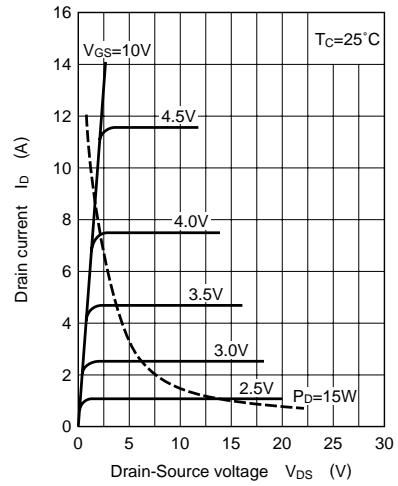
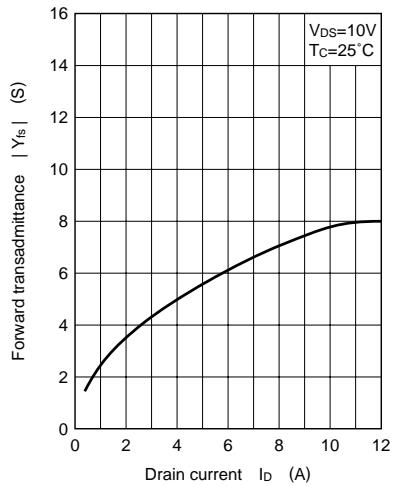
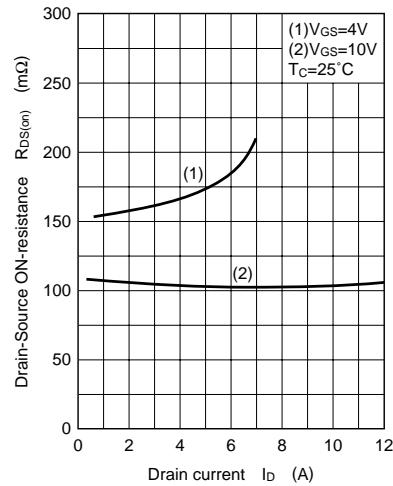
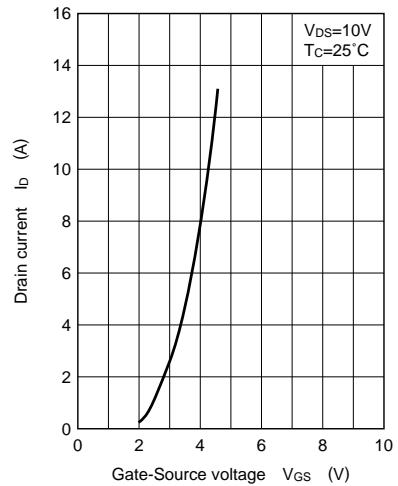
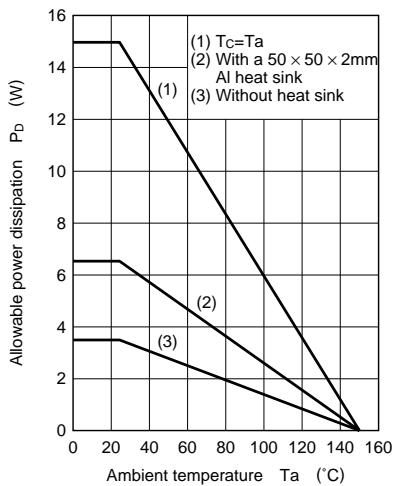
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source cut-off current	$I_{DSS}$	$V_{DS}=20\text{V}$ , $V_{GS}=0$			10	$\mu\text{A}$
Gate-Source leakage current	$I_{GSS}$	$V_{GS}=\pm 20\text{V}$ , $V_{DS}=0$			$\pm 1$	$\mu\text{A}$
Drain-Source breakdown voltage	$V_{DSS}$	$I_D=1\text{mA}$ , $V_{GS}=0$	25		45	V
Gate threshold voltage	$V_{th}$	$V_{DS}=25\text{V}$ , $I_D=1\text{mA}$	1		2.5	V
Drain-Source ON-resistance	$R_{DS(on)1}$	$V_{GS}=10\text{V}$ , $I_D=3\text{A}$		110	140	$\text{m}\Omega$
	$R_{DS(on)2}$	$V_{GS}=4\text{V}$ , $I_D=3\text{A}$		160	220	$\text{m}\Omega$
Forward transadmittance	$ Y_{fs} $	$V_{DS}=25\text{V}$ , $I_D=3\text{A}$	3	5.5		S
Diode forward voltage	$V_{DF}$	$I_{DR}=6\text{A}$ , $V_{GS}=0$			-1.7	V
Input capacitance	$C_{iss}$	$V_{DS}=10\text{V}$ , $V_{GS}=0$ , $f=1\text{MHz}$		40		$\text{pF}$
Output capacitance	$C_{oss}$			300		$\text{pF}$
Feedback capacitance	$C_{rss}$			20		$\text{pF}$
Turn-on time	$t_{on}$	$V_{GS}=10\text{V}$ , $I_D=3\text{A}$ $V_{DD}=30\text{V}$ , $R_L=10\Omega$		1		$\mu\text{s}$
Fall time	$t_f$			2		$\mu\text{s}$
Turn-off time (delay time)	$t_{d(off)}$			1		$\mu\text{s}$



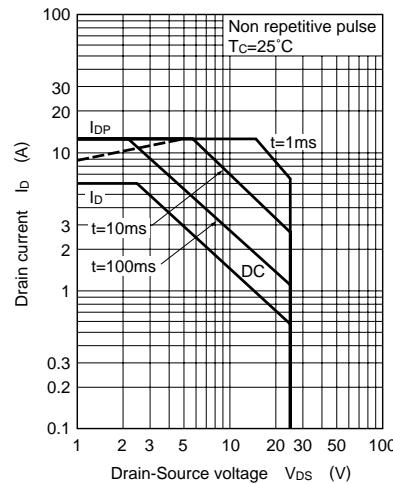
### ■ Internal Connection



Avalanche capability test circuit

 $I_D - V_{DS}$  $|Y_{fs}| - I_D$  $R_{DS(on)} - I_D$  $I_D - V_{GS}$  $P_D - T_a$ 

Area of safe operation (ASO)

 $I_{DR} - V_{SD}$ 